查询2SC4420供应商 Power Transistors

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# 2SC4420

### Silicon NPN triple diffusion planar type

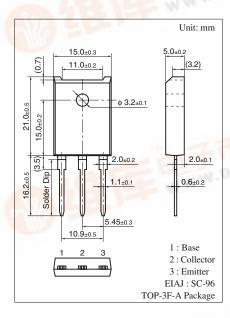
For high breakdown voltage high-speed switching W.DZSC.COM

#### Features

- High-speed switching
- High collector to base voltage V<sub>CBO</sub>
- Wide area of safe operation (ASO)
- Satisfactory linearity of forward current transfer ratio  $h_{FE}$
- Full-pack package which can be installed to the heat sink with one screw

Absolute Maximum Hatings $T_c = 25 C$							
Parameter		Symbol	Rating	Unit			
Collector to base voltage		V <sub>CBO</sub>	900	V			
Collector to emitter voltage		V <sub>CES</sub>	900	V			
	a been it	V <sub>CEO</sub>	800	V			
Emitter to base voltage		V <sub>EBO</sub>	7	V			
Peak collector current		I <sub>CP</sub>	5	А			
Collector current		I <sub>C</sub>	3	А			
Base current		IB	1	А			
Collector power	$T_C = 25^{\circ}C$	P <sub>C</sub>	70	W			
dissipation	$T_a = 25^{\circ}C$	1.0	3				
Junction temperature		Tj	150	°C			
Storage temperature		T <sub>stg</sub>	-55 to +150	°C			

#### Absolute Maximum Ratings $T_c = 25^{\circ}C$

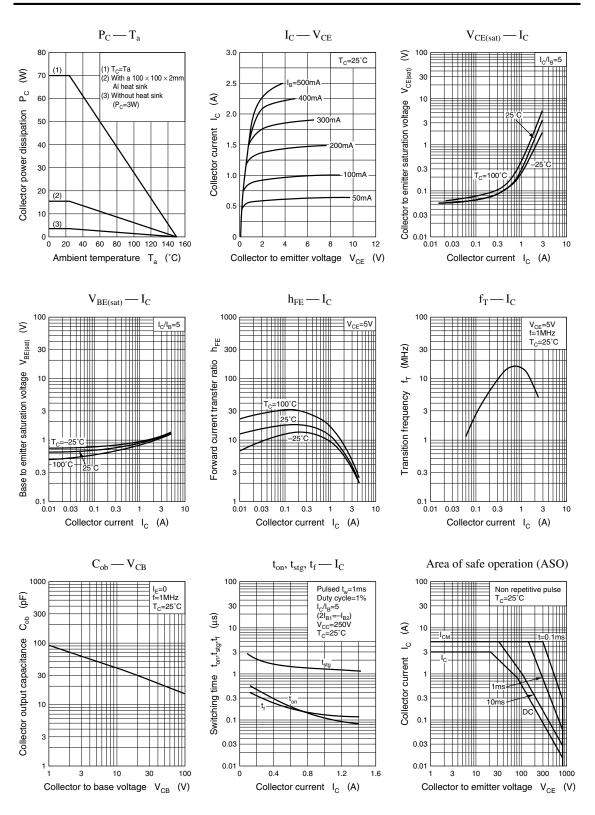


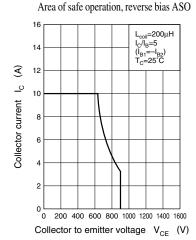
#### **Electrical Characteristics** $T_C = 25^{\circ}C$

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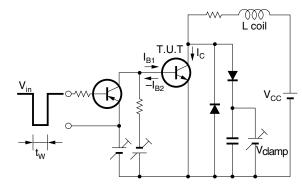
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector cutoff current	I <sub>CBO</sub>	$V_{CB} = 900 \text{ V}, I_E = 0$	-	C C C	50	μA
Emitter cutoff current	I <sub>EBO</sub>	$V_{\rm EB} = 7 \text{ V}, I_{\rm C} = 0$	1		50	μA
Collector to emitter voltage	V <sub>CEO</sub>	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	800			V
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = 5 V, I_C = 0.1 A$	8			
	h <sub>FE2</sub>	$V_{CE} = 5 V, I_C = 0.8 A$	6			
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 0.8 \text{ A}, I_{\rm B} = 0.16 \text{ A}$			1.5	V
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	$I_{\rm C} = 0.8 \text{ A}, I_{\rm B} = 0.16 \text{ A}$			1.5	V
Transition frequency	f <sub>T</sub>	$V_{CE} = 5 V, I_C = 0.15 A, f = 1 MHz$		10		MHz
Turn-on time	t <sub>on</sub>	$I_{C} = 0.8 \text{ A}, I_{B1} = 0.16 \text{ A}, I_{B2} = -0.32 \text{ A},$			0.7	μs
Storage time	t <sub>stg</sub>	$V_{CC} = 250 V$			2.5	μs
Fall time	t <sub>f</sub>				0.3	μs

#### **Power Transistors**

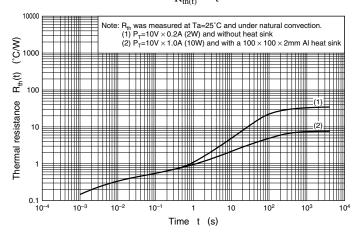




Reverse bias ASO measuring circuit



 $R_{th(t)} - t$ 



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